

## SiC SCHOTTKY DIODE TYPE 8A

### Features

- Low conduction and switching loss
- Zero reverse recovery
- High surge current capability
- Positive temperature coefficient device
- RoHS compliant and halogen free
- Temperature independent switching behavior
- Suitable for high power application
- $V_{DC}$  650 V
- $I_F$  ( $T_C=25 / 144\text{ }^{\circ}\text{C}$ ) 17A/8A

### Benefits

- Increase parallel device convenience
- Enable high temperature application
- Realize compact and lightweight systems
- Allow high frequency operation
- Higher system efficiency
- High reliability

### Applications

- Switching mode power supply
- PFC
- UPS
- Motor drives
- Flywheel diode in power inverters
- Solar/Wind renewable energy

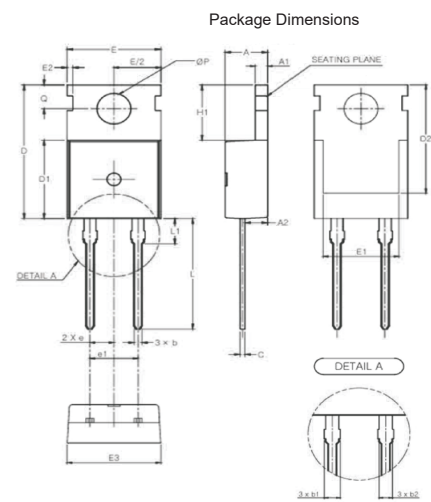
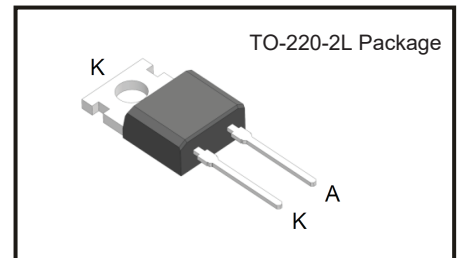
### Maximum Ratings

Operating Junction Temperature :  $-55^{\circ}\text{C}$  to  $+175^{\circ}\text{C}$

Storage Temperature :  $-55^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
CSR008-065C3	650V	650V

Maximum Rating	Symbol	Conditions	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	$T_J=25\text{ }^{\circ}\text{C}$	650	V
Continuous forward current	$I_F$	$T_C=25\text{ }^{\circ}\text{C}$	17	A
		$T_C=144\text{ }^{\circ}\text{C}$	8	
Non-repetitive forward surge current	$I_{FSM}$	$T_C=25\text{ }^{\circ}\text{C}$ , $t_p=10\mu\text{s}$	65	
Non-repetitive forward surge current	$I_{Fmax.}$	$T_C=25\text{ }^{\circ}\text{C}$ , $t_p=10\mu\text{s}$	600	
Power Dissipation	$P_D$	$T_C=25\text{ }^{\circ}\text{C}$	75	W



Unit : mm

SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.90
b1	1.42	1.52	1.62
b2	1.17	1.27	1.37
c	0.45	0.50	0.60
D	15.50	15.70	15.90
D1	9.00	9.20	9.40
D2	(12.70)		
E	9.70	9.90	10.10
E1	(8.00)		
E2	(0.60)		
E3	9.70	9.90	10.10
e	2.54 BSC		
e1	5.08 BSC		
H1	6.30	6.50	6.70
L	12.88	13.08	13.28
L1	(3.00)		
QP	3.50	3.60	3.70
Q	2.70	2.80	2.90

**Electrical Characteristics**, at  $T_J = 25^\circ\text{C}$ , unless otherwise specified.

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	$V_{DC}$		650	-	-	V
Diode forward voltage	$V_F$	$I_F = 8\text{A}$ , $T_J = 25^\circ\text{C}$	-	1.3	1.5	
		$I_F = 8\text{A}$ , $T_J = 175^\circ\text{C}$	-	1.6	-	
Reverse current	$I_R$	$V_R = 650\text{V}$ , $T_J = 25^\circ\text{C}$	-	1	50	$\mu\text{A}$
		$V_R = 650\text{V}$ , $T_J = 175^\circ\text{C}$	-	5	200	

**AC Characteristics**

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Total capacitive charge	$Q_C$	$V_R = 400\text{V}$	-	16	-	nC
Total capacitance	C	$V_R = 0\text{V}$ , $f = 1\text{ MHz}$	-	480	-	pF
		$V_R = 400\text{V}$ , $f = 1\text{ MHz}$	-	42	-	
Total capacitive energy	$E_C$	$V_R = 400\text{V}$	-	5	-	$\mu\text{J}$

**Thermal Characteristics**

Static Characteristics	Symbol	Values	Unit
		max.	
Thermal resistance from junction to case	$R_{\theta JC}$	2.0	$^\circ\text{C/W}$

## Typical Device Performance

Fig. 1 Typical Forward Characteristics ( $I_F=f(V_F)$ ,  $t_p=20\mu s$ )

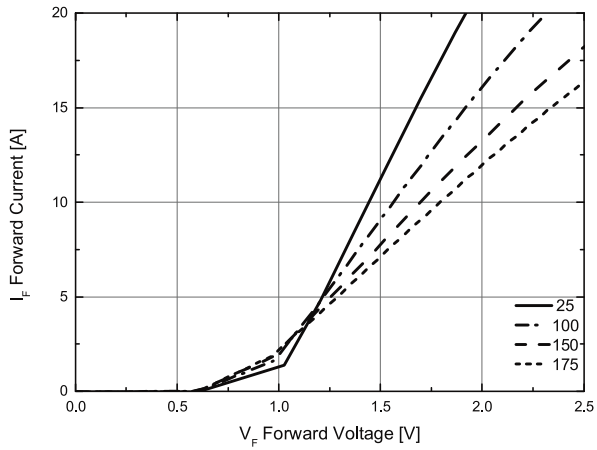


Fig. 2 Typical Reverse Current as Function of Reverse Voltage

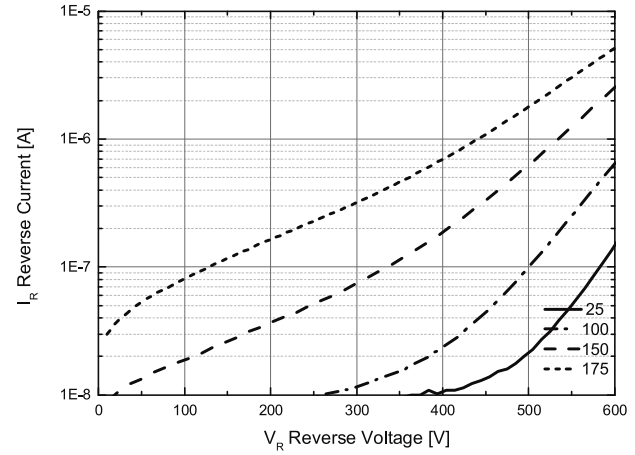


Fig. 3 Diode Forward Current as Function of Temperature

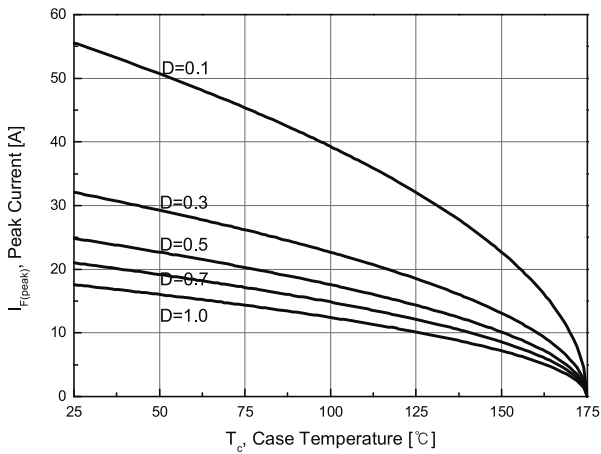


Fig. 4 Typical Capacitance as Function of Reverse Voltage

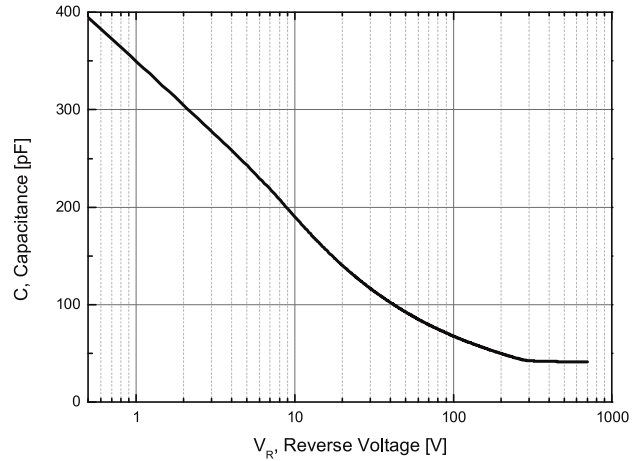


Fig. 5 Typical capacitive charge

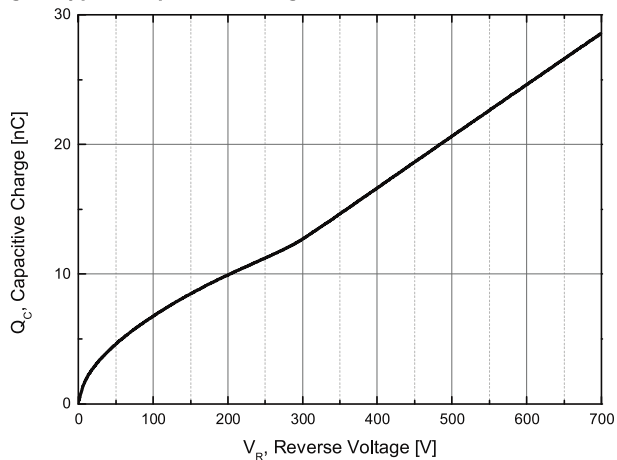
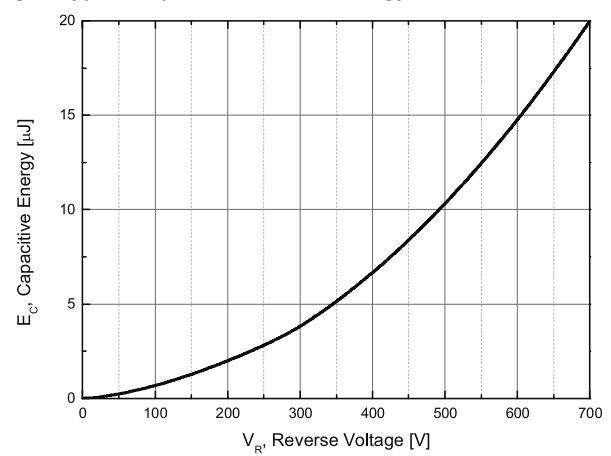


Fig. 6 Typical capacitance stored energy



## Typical Device Performance

Fig. 7 Power Dissipation as Function of Case Temperature

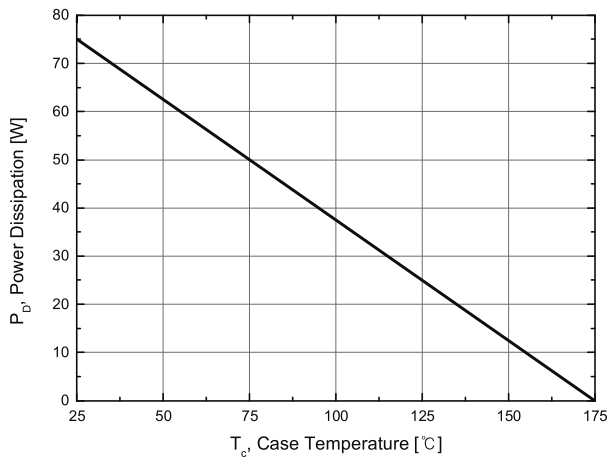
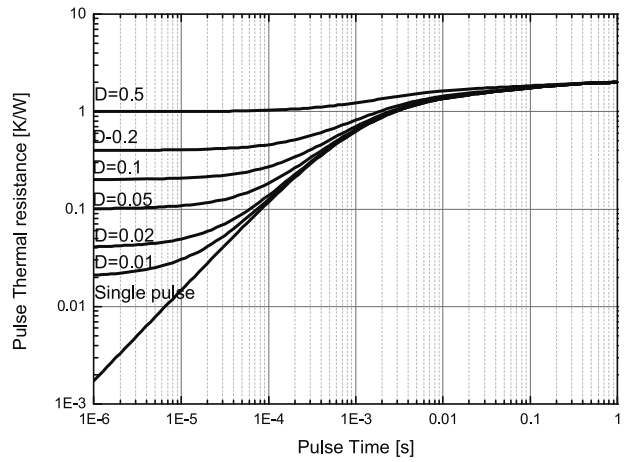


Fig. 8 Transient Thermal impedance



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